

74AHC257; 74AHCT257

Quad 2-input multiplexer; 3-state

Rev. 02 — 9 May 2008

Product data sheet

1. General description

The 74AHC257; 74AHCT257 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC257; 74AHCT257 has four identical 2-input multiplexers with 3-state outputs, which select 4 bits of data from two sources and are controlled by a common data select input (S). The data inputs from source 0 (1I0 to 4I0) are selected when input S is LOW and the data inputs from source 1 (1I1 to 4I1) are selected when input S is HIGH. Data appears at the outputs (1Y to 4Y) in true (non-inverting) form from the selected inputs. The 74AHC257; 74AHCT257 is the logic implementation of a 4-pole 2-position switch, where the position of the switch is determined by the logic levels applied to input S. The outputs are forced to a high-impedance OFF-state when $\overline{OE}$ is HIGH.

The logic equations for the outputs are:

$$1Y = \overline{OE} \times (1I1 \times S + 1I0 \times \overline{S})$$

$$2Y = \overline{OE} \times (2I1 \times S + 2I0 \times \overline{S})$$

$$3Y = \overline{OE} \times (3I1 \times S + 3I0 \times \overline{S})$$

$$4Y = \overline{OE} \times (4I1 \times S + 4I0 \times \overline{S})$$

The 74AHC257; 74AHCT257 is identical to the 74AHC258; 74AHCT258, but has non-inverting (true) outputs.

2. Features

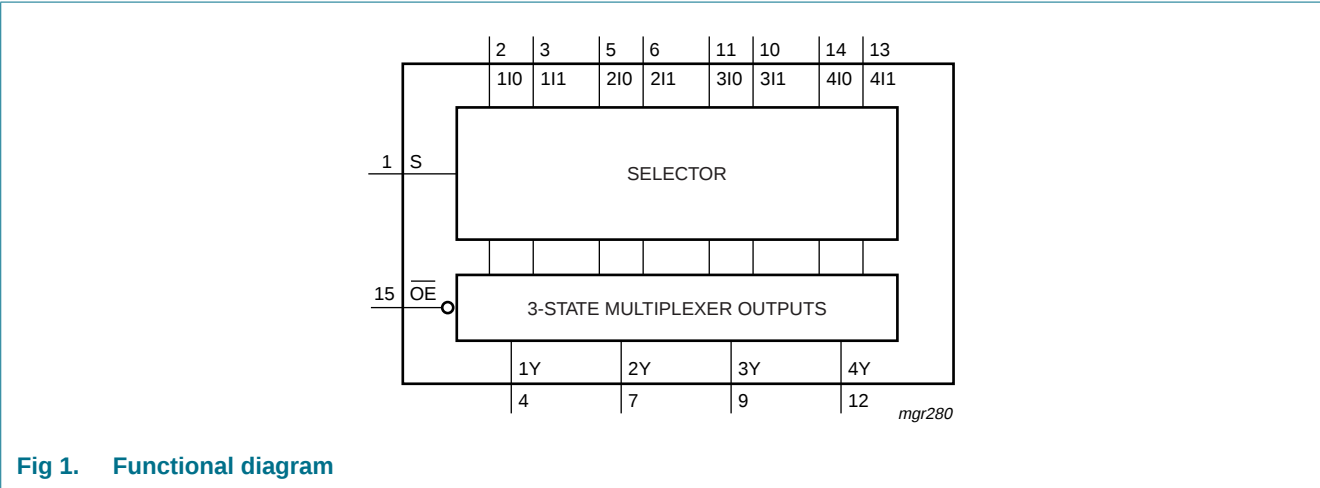
- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Non-inverting data path
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - ◆ For 74AHC257: CMOS level
 - ◆ For 74AHCT257: TTL level
- ESD protection:
 - ◆ HBM EIA/JESD22-A114E exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V
 - ◆ CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC257				
74AHC257D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74AHC257PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74AHCT257				
74AHCT257D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74AHCT257PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram



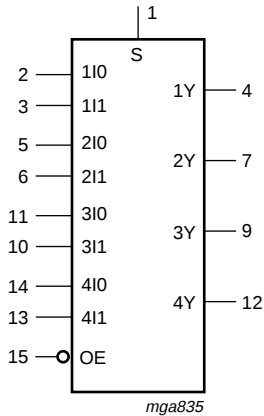


Fig 2. Logic symbol

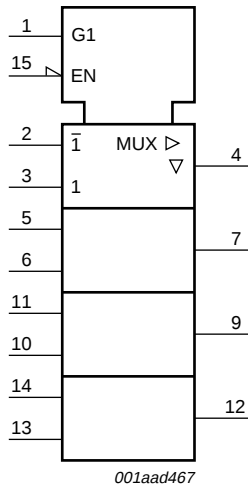


Fig 3. IEC logic symbol

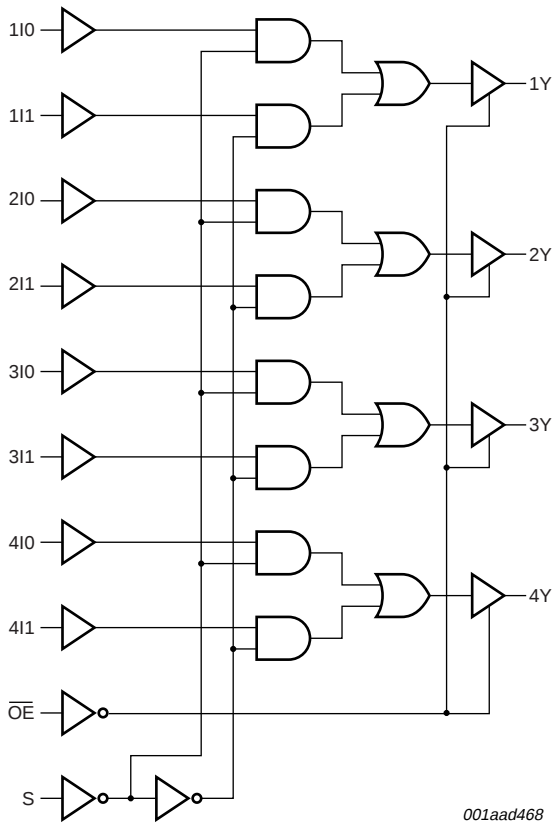
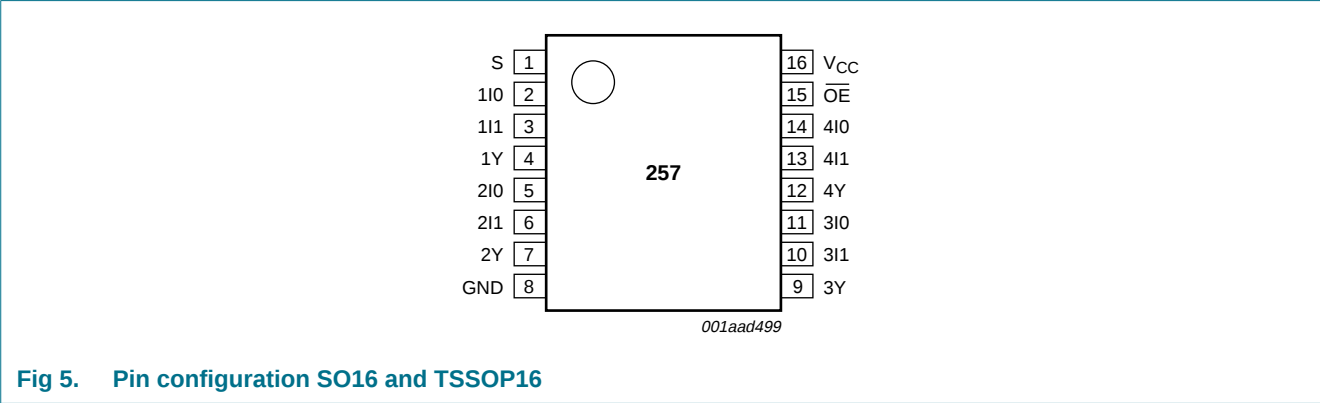


Fig 4. Logic diagram

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
S	1	common data select input
1I0	2	data input from source 0
1I1	3	data input from source 1
1Y	4	multiplexer output
2I0	5	data input from source 0
2I1	6	data input from source 1
2Y	7	multiplexer output
GND	8	ground (0 V)
3Y	9	multiplexer output
3I1	10	data input from source 1
3I0	11	data input from source 0
4Y	12	multiplexer output
4I1	13	data input from source 1
4I0	14	data input from source 0
OE	15	output enable input (active LOW)
VCC	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Control		Input		Output
$\overline{\text{OE}}$	S	nI0	nI1	nY
H	X	X	X	Z
L	H	X	L	L
		X	H	H
	L	L	X	L
		H	X	H

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5 \text{ V}$	^[1] -20	-	mA
I_{OK}	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{CC} + 0.5 \text{ V}$	^[1] -20	+20	mA
I_O	output current	$V_O = -0.5 \text{ V}$ to $(V_{CC} + 0.5 \text{ V})$	-25	+25	mA
I_{CC}	supply current		-	+75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40 \text{ °C}$ to $+125 \text{ °C}$	^[2] -	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
 For TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74AHC257						
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	20	ns/V
74AHCT257						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC257										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −50 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −50 μA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = −50 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I _O = −8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.80	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL};$ $V_O = V_{CC} \text{ or GND};$ $V_{CC} = 5.5 \text{ V}$	-	-	± 0.25	-	± 2.5	-	± 10.0	μA
I_{CC}	supply current	$V_I = V_{CC} \text{ or GND}; I_O = 0 \text{ A};$ $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	μA
C_I	input capacitance	$V_I = V_{CC} \text{ or GND}$	-	3	10	-	10	-	10	pF
C_O	output capacitance		-	4	-	-	-	-	-	pF
74AHCT257										
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
		$I_O = -50 \mu\text{A}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
		$I_O = 50 \mu\text{A}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL};$ $V_O = V_{CC} \text{ or GND per input pin};$ other inputs at $V_{CC} \text{ or GND}; I_O = 0 \text{ A};$ $V_{CC} = 5.5 \text{ V}$	-	-	± 0.25	-	± 2.5	-	± 10.0	μA
I_{CC}	supply current	$V_I = V_{CC} \text{ or GND}; I_O = 0 \text{ A};$ $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	μA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V};$ other pins at $V_{CC} \text{ or GND};$ $I_O = 0 \text{ A}; V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance	$V_I = V_{CC} \text{ or GND}$	-	3	10	-	10	-	10	pF
C_O	output capacitance		-	4	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74AHC257										
t _{pd}	propagation delay	nI0, nI1 to nY; see Figure 6 ^[2]								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	4.2	9.3	1.0	11.0	1.0	12.0	ns
		C _L = 50 pF	-	6.0	12.8	1.0	14.5	1.0	16.0	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	2.9	5.9	1.0	7.0	1.0	7.5	ns
		C _L = 50 pF	-	4.2	7.9	1.0	9.0	1.0	11.5	ns
		S to nY; see Figure 6 ^[2]								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	5.2	11.0	1.0	13.0	1.0	14.0	ns
		C _L = 50 pF	-	7.4	14.5	1.0	16.5	1.0	18.5	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.5	6.8	1.0	8.0	1.0	8.5	ns
		C _L = 50 pF	-	5.0	8.8	1.0	10.0	1.0	12.5	ns
t _{en}	enable time	$\overline{\text{OE}}$ to nY; see Figure 7 ^[3]								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	4.5	10.5	1.0	12.5	1.0	13.5	ns
		C _L = 50 pF	-	6.4	14.0	1.0	16.0	1.0	17.5	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.2	6.8	1.0	8.0	1.0	8.5	ns
		C _L = 50 pF	-	4.5	8.8	1.0	10.0	1.0	12.5	ns
t _{dis}	disable time	$\overline{\text{OE}}$ to nY; see Figure 7 ^[4]								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	5.1	9.5	1.0	11.0	1.0	11.5	ns
		C _L = 50 pF	-	7.2	12.0	1.0	13.5	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.4	6.5	1.0	7.0	1.0	8.5	ns
		C _L = 50 pF	-	4.9	7.9	1.0	9.0	1.0	9.5	ns
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC} ^[5]								
		4 outputs switching via input S	-	45	-	-	-	-	-	pF
		1 output switching via input I	-	15	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74AHCT257; V _{CC} = 4.5 V to 5.5 V										
t _{pd}	propagation delay	nI0, nI1 to nY; see Figure 6 ^[2]								
		C _L = 15 pF	-	3.7	6.5	1.0	8.0	1.0	9.0	ns
		C _L = 50 pF	-	4.9	8.5	1.0	10.0	1.0	11.0	ns
		S to nY; see Figure 6 ^[2]								
		C _L = 15 pF	-	5.1	9.0	1.0	10.5	1.0	11.5	ns
		C _L = 50 pF	-	6.4	10.5	1.0	12.5	1.0	13.5	ns
t _{en}	enable time	OE to nY; see Figure 7 ^[3]								
		C _L = 15 pF	-	3.9	8.0	1.0	9.0	1.0	10.0	ns
		C _L = 50 pF	-	5.1	10.0	1.0	11.0	1.0	12.0	ns
t _{dis}	disable time	OE to nY; see Figure 7 ^[4]								
		C _L = 15 pF	-	4.5	7.5	1.0	8.0	1.0	8.5	ns
		C _L = 50 pF	-	6.5	9.5	1.0	10.5	1.0	11.5	ns
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC} ^[5]								
		4 outputs switching via input S	-	51	-	-	-	-	-	pF
		1 output switching via input I	-	15	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).[2] t_{pd} is the same as t_{PLH} and t_{PHL}.[3] t_{en} is the same as t_{pZL} and t_{pZH}.[4] t_{dis} is the same as t_{PLZ} and t_{PHZ}.[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).P_D = C_{PD} × V_{CC}² × f_i × N + Σ(C_L × V_{CC}² × f_o) where:f_i = input frequency in MHz;f_o = output frequency in MHz;C_L = output load capacitance in pF;V_{CC} = supply voltage in V;

N = number of inputs switching;

Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

11. Waveforms

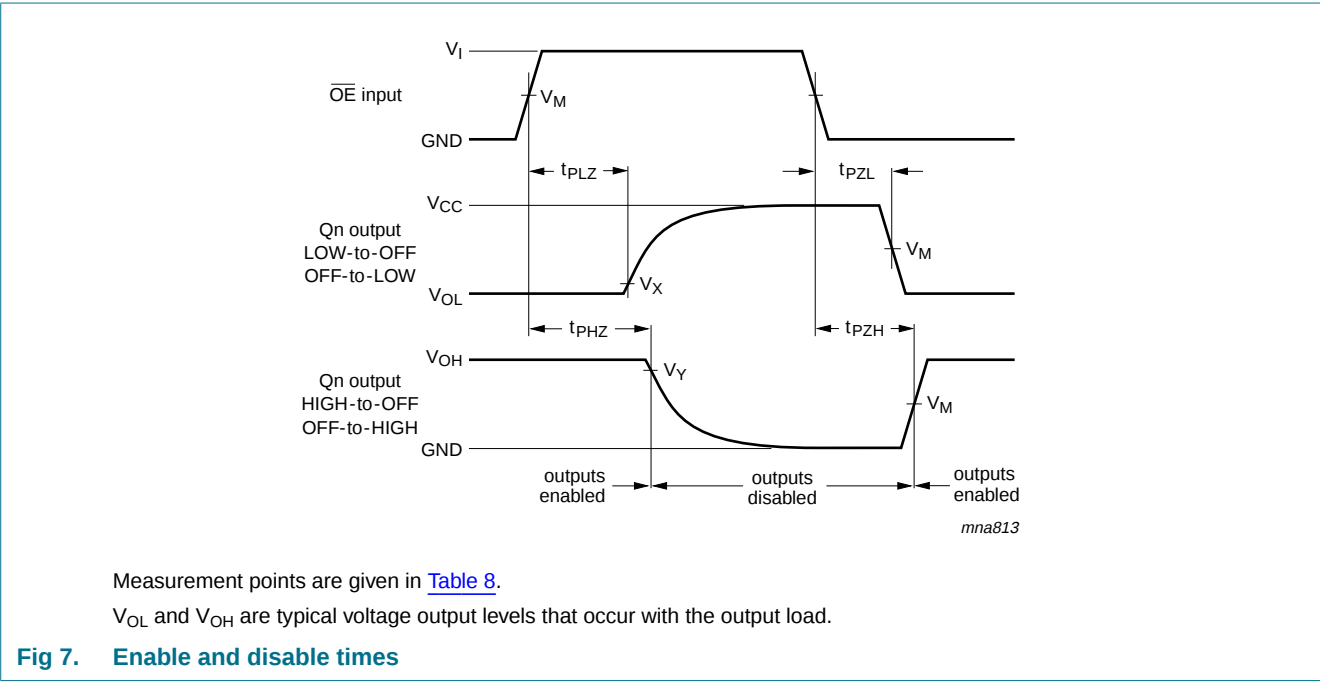
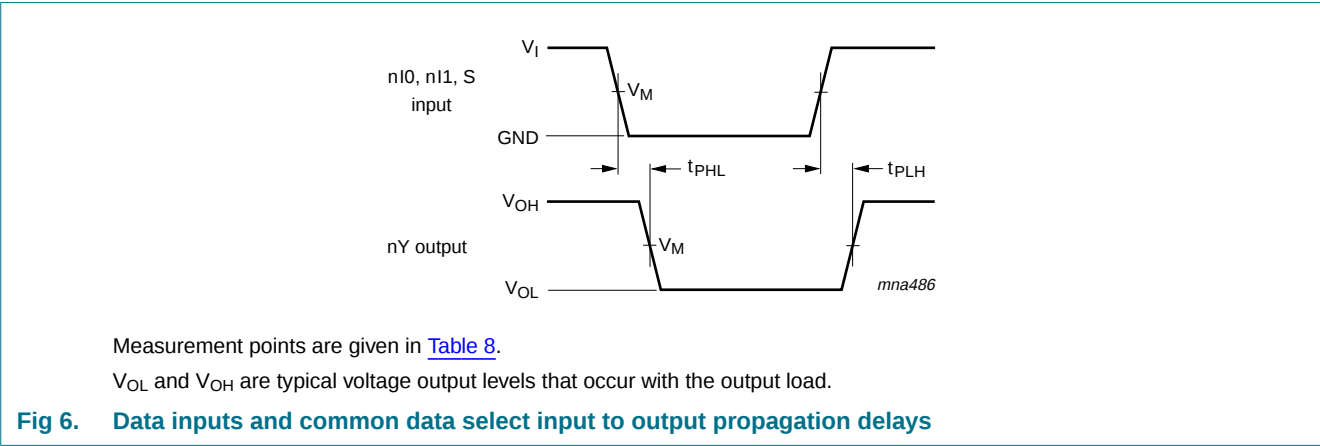
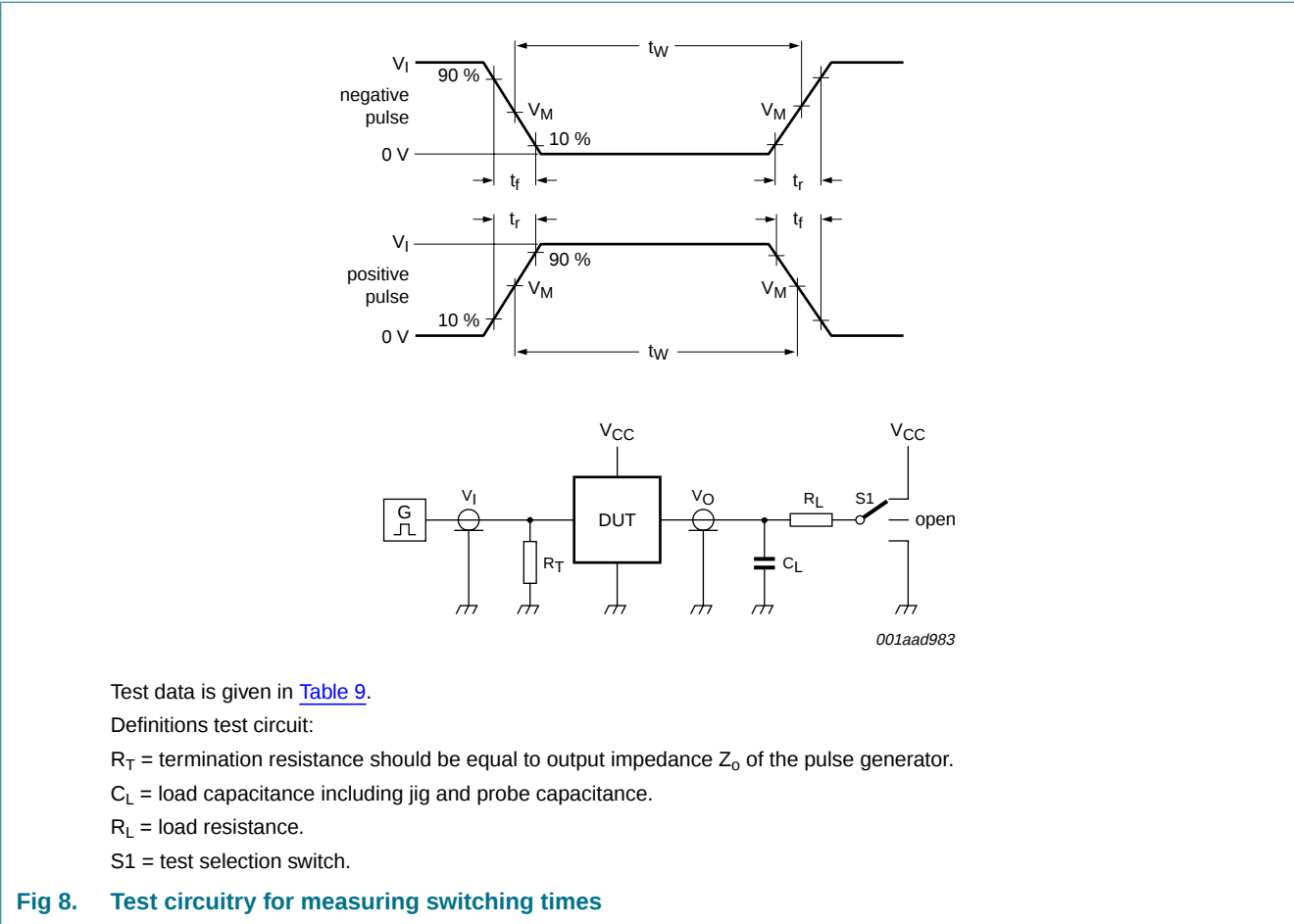


Table 8. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74AHC257	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$
74AHCT257	1.5 V	$0.5 \times V_{CC}$	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = load capacitance including jig and probe capacitance.

R_L = load resistance.

$S1$ = test selection switch.

Fig 8. Test circuitry for measuring switching times

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC257	V_{CC}	$\leq 3.0 \text{ ns}$	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74AHCT257	3.0 V	$\leq 3.0 \text{ ns}$	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm SOT109-1

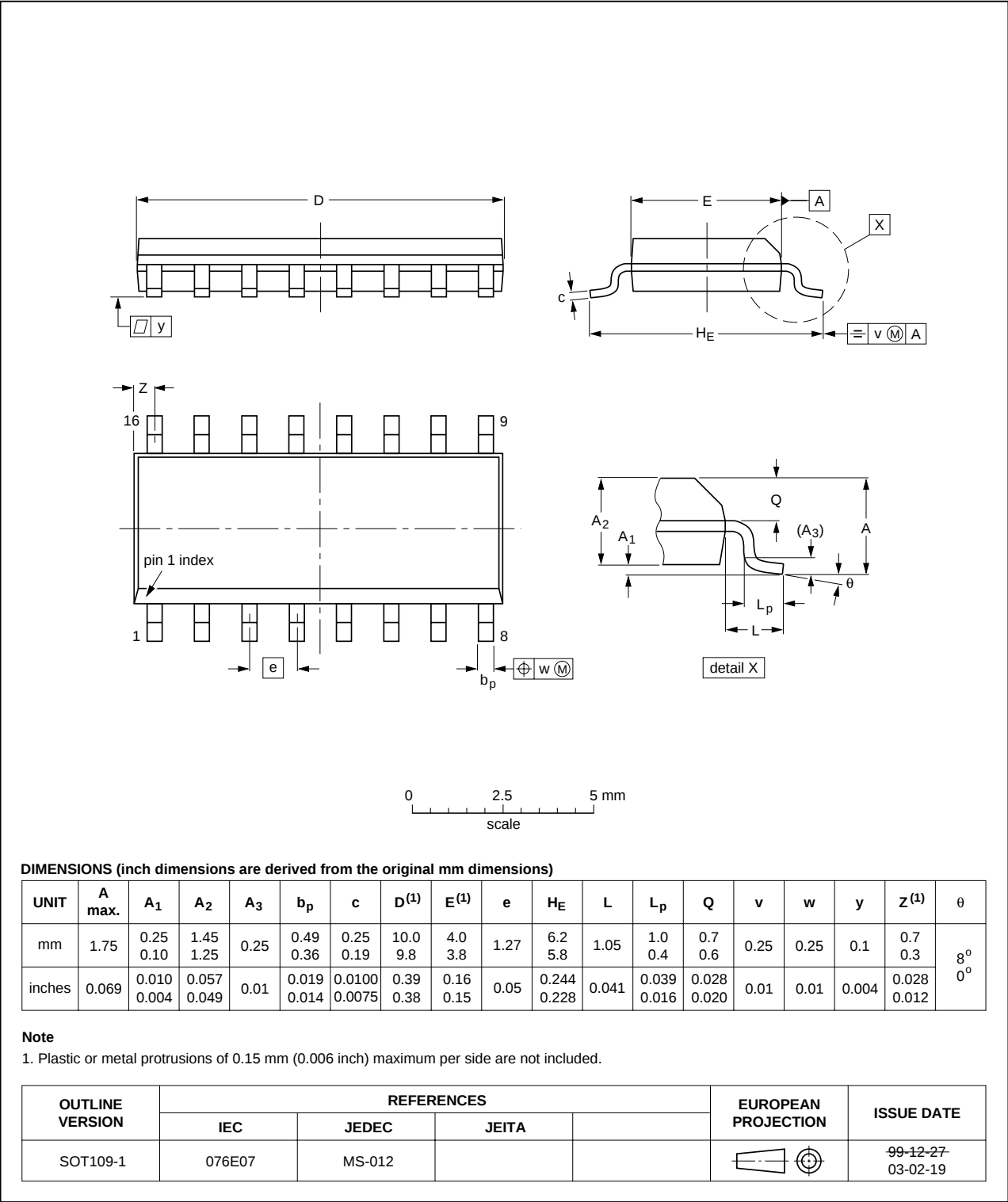


Fig 9. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

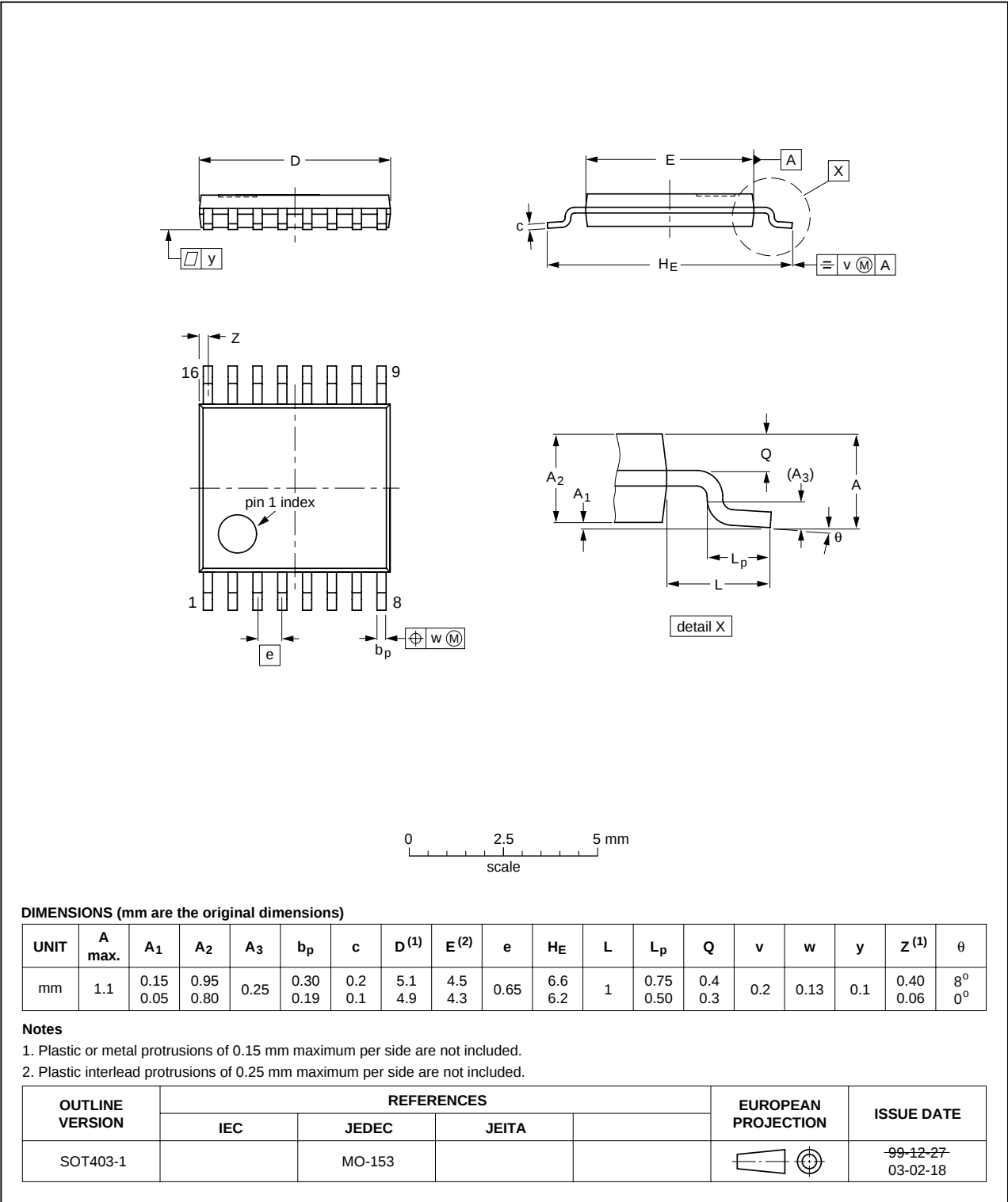


Fig 10. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT257_2	20080509	Product data sheet	-	74AHC_AHCT257_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 6: the conditions for input leakage current have been changed.			
74AHC_AHCT257_1	20000403	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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